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	Ш			OTHER	DOCUMENTOS (T. 1. 1)					
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Article entitled "High-Power Temperature-Insensitive Gain-Off Lasers", dated February 1993, IEEE Photonics Technology Let D.B. Young, J.W. Scott, B.J. Thibeault, S.W. Corzine, M.G. Pet				tive Gain-Offset InGaAs / C chnology Letters Engineeri ne, M.G. Peters, S.L. Lee, a	GaAs Verticing Periodicand L.A. Co	al-Cavity Surfaction of the second se	re-Emitting pages 129-	132, by		
4n	Article entitled "Enhanced Performance of Offset-Gain High-Barrier Vertical-Cavity Surface-Emitting Lasers", dated June 1993, IEEE Journal of Quantum Electronics, Volume 29, Number 6, pages 2013-2022, by D.B. Young, J.W. Scott, F.H. Peters, M.G. Peters, M.L. Majewski, B.J. Thibeault, Scott W. Corzine, and Larry A. Coldren									
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			Docket Number (Optional) 15436.170.1	Application Number 10/695,057				
INF		ATION DISCLOSURE CITATION	Applicant(s)					
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*EXAMINER INITIAL		OTHER DOCUMENTS (Including Author, Titl	le, Date, Pertinent Pages, Etc.)	·				
gh.	4	Article entitled "Highly Efficient Vertical-Cavity St dated August 1995, IEEE Photonics Technology Le L.A. Coldren	Surface-Emitting Lasers Optimized for Low-Temperature Operation", etters, Vol. 7, No. 8, pages 851-853, by E. Goobar, M.G. Peters, G. Fish, and					
M	5	Article entitled "Low-Temperature (10-300 K) Cha Lasers", dated October 1995, IEEE Photonics Tech Barr, W.D. Cox, K.S. Brown, R.A. Morgan, and M.	itled "Low-Temperature (10-300 K) Characterization of MOVPE-Grown Vertical-Cavity Surface-Emitting ated October 1995, IEEE Photonics Technology Letters, Vol. 7, No. 10, pages 1110-1112, by L.A. Hornak, J.C Cox, K.S. Brown, R.A. Morgan, and M.K. Hibbs-Brenner					
en		Article entitled "Cryogenic Operation of A1GaAs- to 6 K, dated March 1996, IEEE Photonics Technol Luo, Julian Cheng, S. Hersee, S.Z. Sun, R.P. Schnei	Operation of A1GaAs-GaAs Vertical-Cavity Surface-Emitting Lasers at Temperatures from 200 K EEE Photonics Technology Letters, Vol. 8, No. 3, pages 316-318, by G. Goncher, Bo Lu, Wen-Lin e, S.Z. Sun, R.P. Schneider, and J.C. Zolper					
en	7	Article entitled "Temperature Sensitivity of 1.54 un October 1997, IEEE Journal of quantum Electronic Klaus Streubel, Janos Andre and J. Wallin	n Vertical-Cavity Lasers with an InP- s, Vol. 33, No. 10, pages 1839-1845, b	Based Bragg Reflector", dated y Stefan Rapp, Joachim Piprek,				
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